

# INK0102AC1

High speed switching  
Silicon N-channel MOSFET

## DESCRIPTION

INK0102AC1 is a Silicon N-channel MOSFET.

This product is most suitable for low voltage use such as portable machinery, because of low voltage drive and low resistance.

## FEATURE

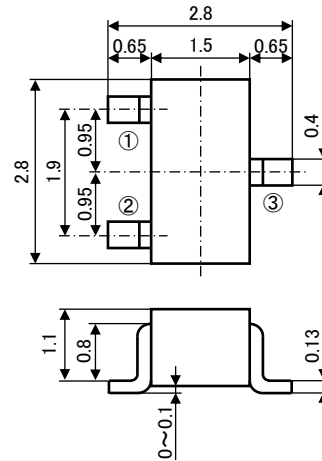
- Input impedance is high, and not necessary to consider a drive electric current.
- Drive voltage 2.5V
- Low on Resistance.  
 $R_{DS(ON)}=0.35\ \Omega$  (TYP) @ $I_D=0.2A, V_{GS}=4.5V$   
 $R_{DS(ON)}=0.48\ \Omega$  (TYP) @ $I_D=0.1A, V_{GS}=2.5V$
- High speed switching.
- Small packing for easy mounting.

## APPLICATION

Inductive loads switching

## OUTLINE DRAWING

Unit: mm



JEITA—: SC-59

JEDEC: Similar to TO-236

TERMINAL CONNECTOR

①: GATE

②: SOURCE

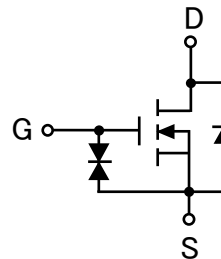
③: DRAIN

## MAXIMUM RATINGS (Ta=25°C)

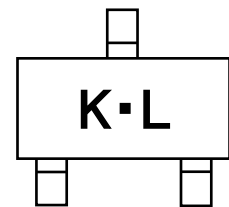
Parameter	Symbol	Rating	Unit
Drain-Source voltage	V <sub>DSS</sub>	30	V
Gate-Source voltage	V <sub>GS</sub>	±8	V
Drain current(DC)	I <sub>D</sub>	0.68	A
Drain current(Pulse)	I <sub>DP</sub>	2(※1)	A
Total power dissipation	P <sub>D</sub>	200	mW
Channel temperature	T <sub>ch</sub>	+150	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

※1: Pw ≤ 10 μs, Duty cycle ≤ 1%

## EQUIVALENT CIRCUIT



## MARKING



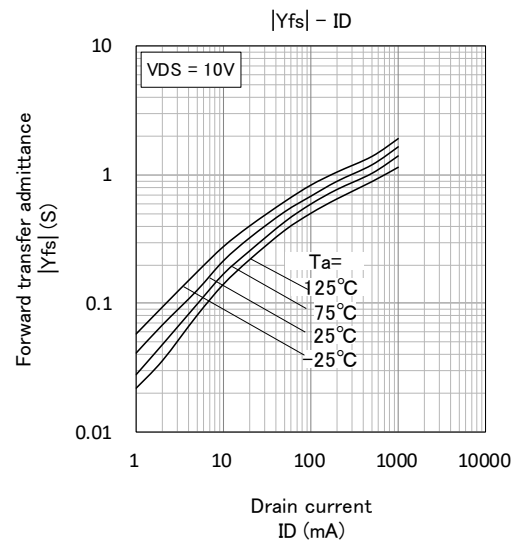
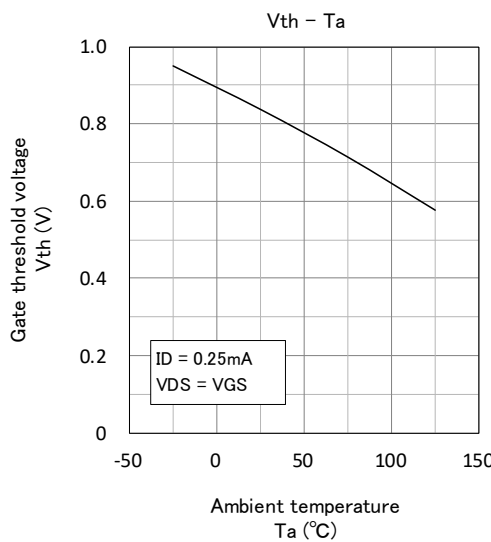
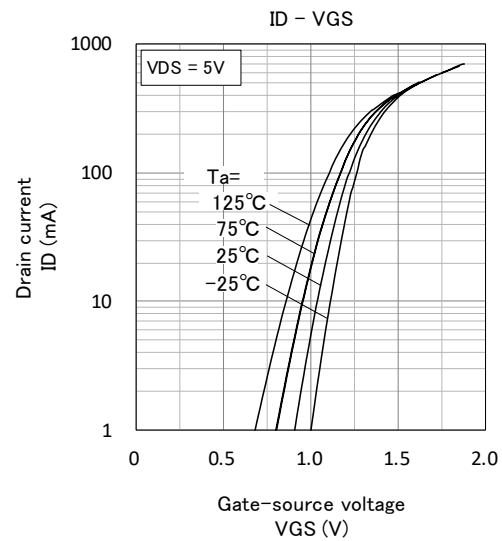
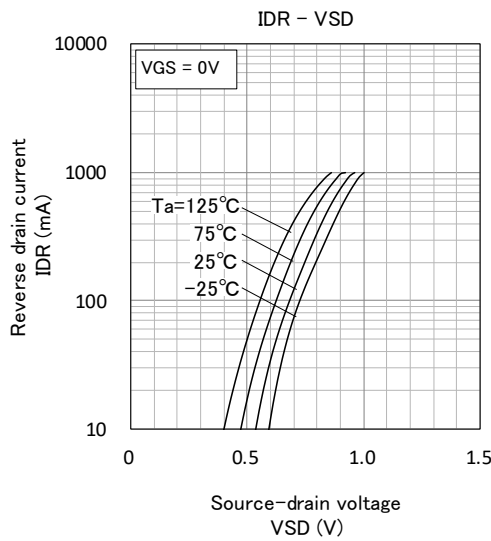
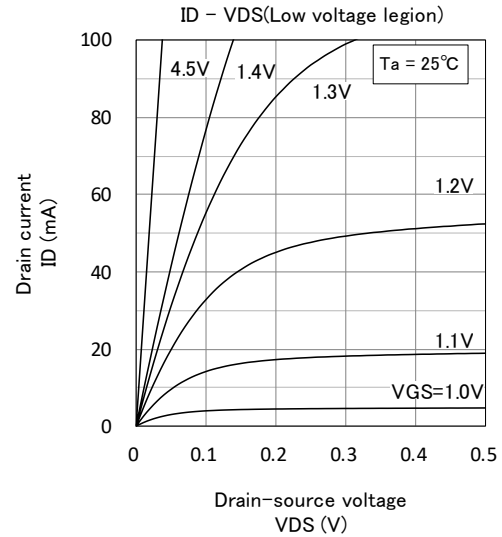
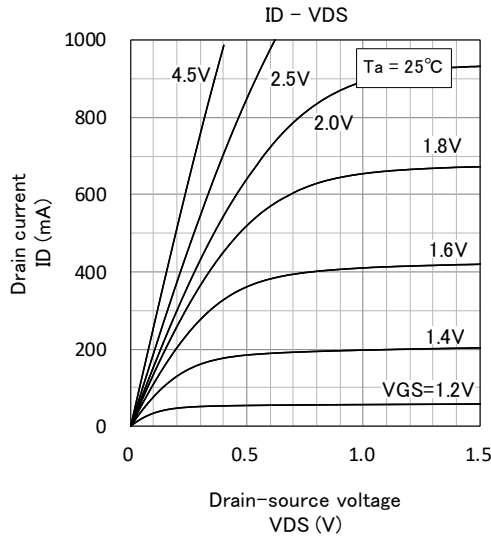
## ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =100μA, V <sub>GS</sub> =0V	30	-	-	V
Gate-Source leak current	I <sub>GS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V	-	-	±10	μA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	μA
Gate threshold voltage	V <sub>th</sub>	I <sub>D</sub> =250μA, V <sub>DS</sub> =V <sub>GS</sub>	0.4	-	1.1	V
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =0.1A	-	700	-	mS
Static Drain-Source on-state resistance	R <sub>DS(ON)</sub>	I <sub>D</sub> =0.2A, V <sub>GS</sub> =4.5V	-	0.35	0.5	Ω
		I <sub>D</sub> =0.1A, V <sub>GS</sub> =2.5V	-	0.48	0.7	
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz	-	62	-	pF
Output capacitance	C <sub>oss</sub>		-	10	-	
Switching time	t <sub>on</sub>	V <sub>DD</sub> =10V, I <sub>D</sub> =0.5A	-	23	-	ns
	t <sub>off</sub>	V <sub>GS</sub> =0~4.5V	-	28	-	

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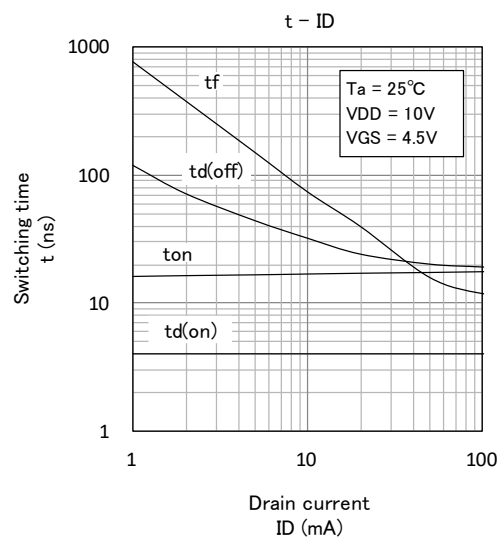
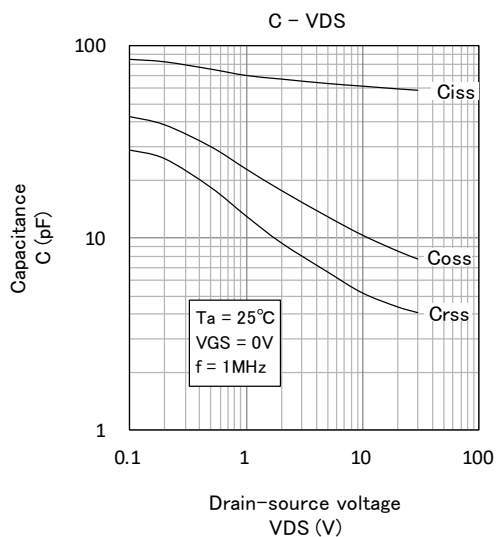
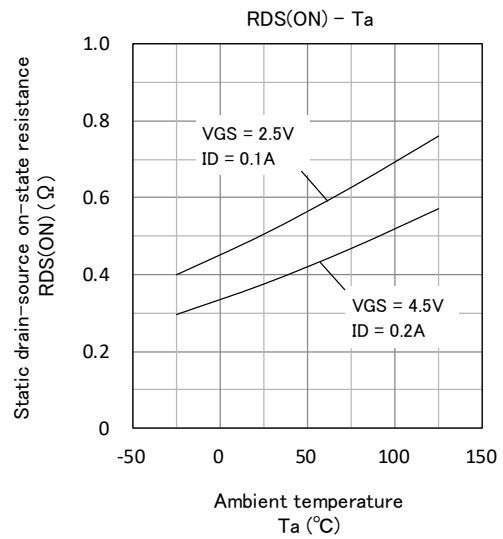
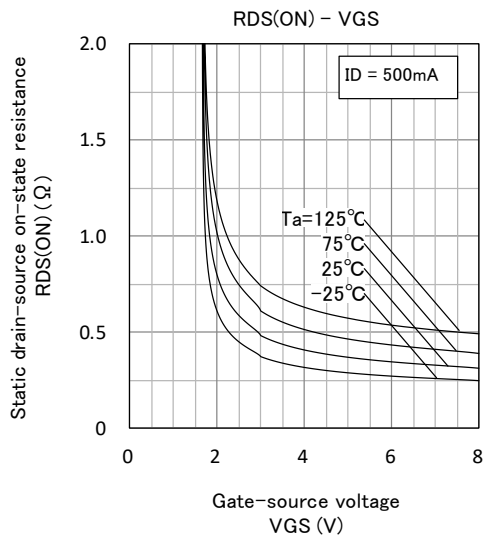
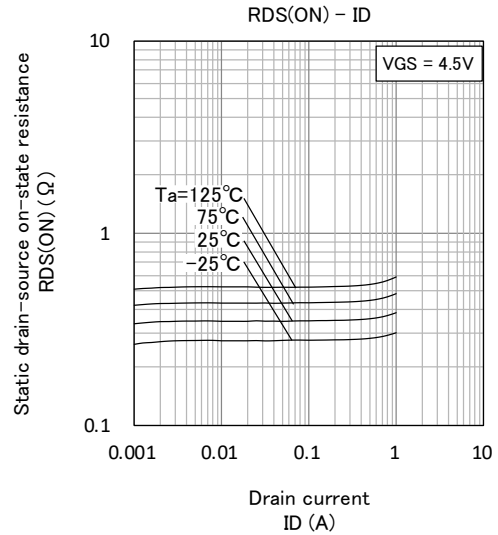
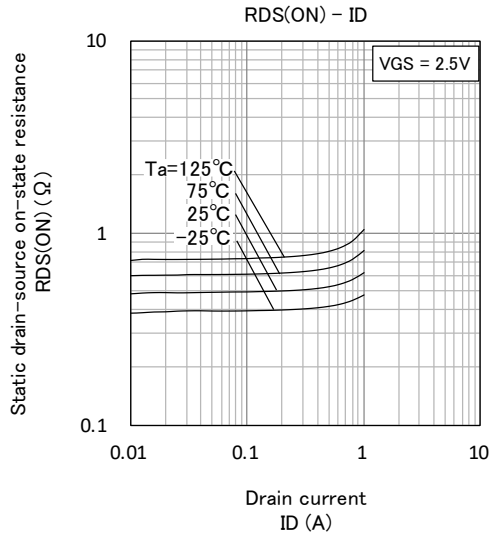
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## TYPICAL CHARACTERISTICS



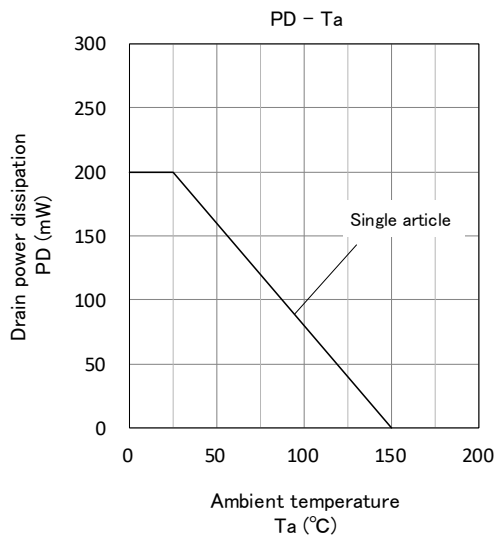
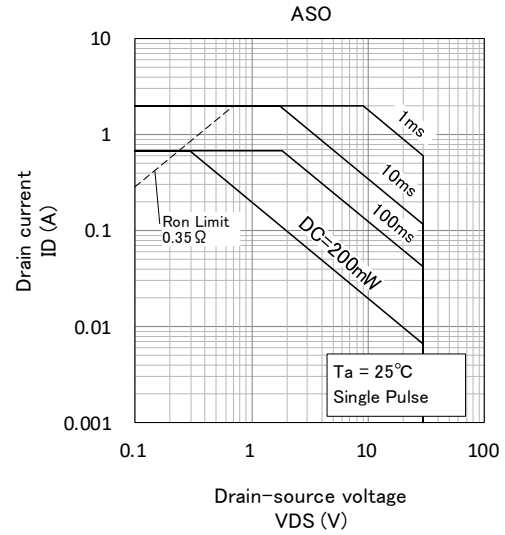
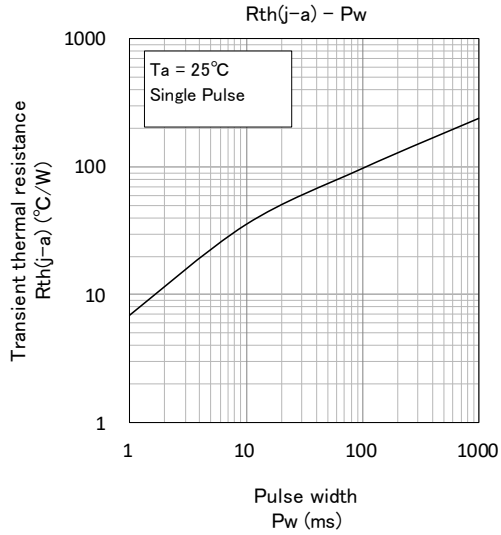
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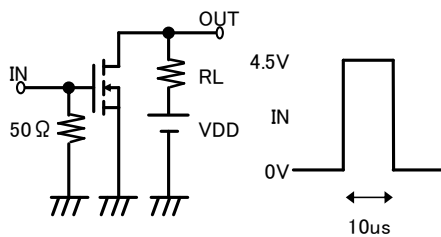


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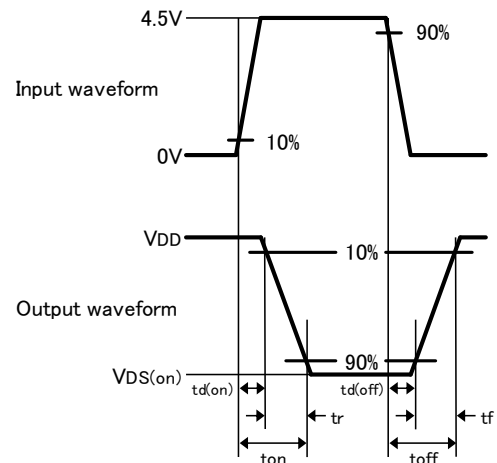
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### Switching time test condition



Duty  $\leq 1\%$   
Input:  $t_r, t_f < 10\text{ns}$   
VDD = 10V  
Common source  
 $T_a = 25^{\circ}\text{C}$



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